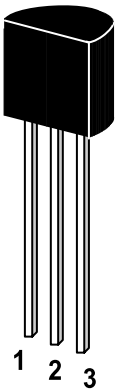


ST 2SD655

NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

The transistor is subdivided into three groups, D, E and F, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

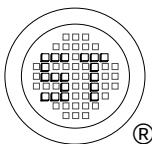


1. Emitter 2. Collector 3. Base

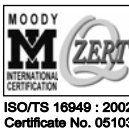
TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	15	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	700	mA
Collector Peak Current	$i_{c(peak)}$	1000	mA
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^{\circ}\text{C}$



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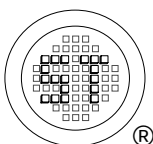


Dated : 07/12/2002

ST 2SD655

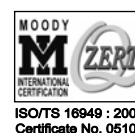
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=1\text{V}$, $I_C=150\text{mA}$					
Current Gain Group D	h_{FE}	250	-	500	-
E	h_{FE}	400	-	800	-
F	h_{FE}	600	-	1200	-
Collector to Base Breakdown Voltage at $I_C=10\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector to Emitter Breakdown Voltage at $I_C=1\text{mA}$	$V_{(BR)CEO}$	15	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current at $V_{CB}=20\text{V}$	I_{CBO}	-	-	1	μA
Base Emitter Voltage at $V_{CE}=1\text{V}$, $I_C=150\text{mA}$	V_{BE}	-	-	1	V
Collector Emitter Saturation Voltage at $I_C=500\text{mA}$, $I_B=50\text{mA}$	$V_{CE(sat)}$	-	0.15	0.5	V
Gain Bandwidth Product at $V_{CE}=1\text{V}$, $I_C=150\text{mA}$	f_T	-	250	-	MHz



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